PROCESS **CP225**

Small Signal Transistor

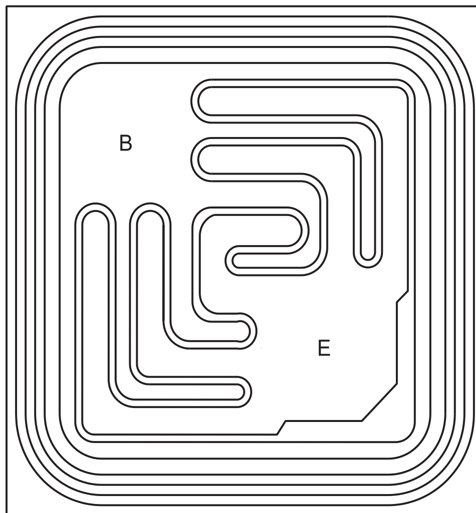
NPN - Amp/Switch Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19.8 x 19.8 MILS
Die Thickness	9.5 MILS
Base Bonding Pad Area	4.3 x 4.3 MILS
Emitter Bonding Pad Area	4.3 x 4.3 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR

R1

GROSS DIE PER 4 INCH WAFER
28,960

PRINCIPAL DEVICE TYPES
2N2218A
2N2221A

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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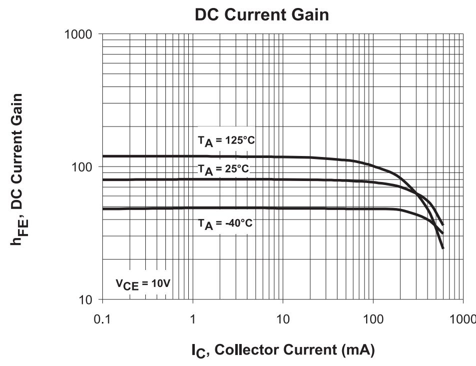
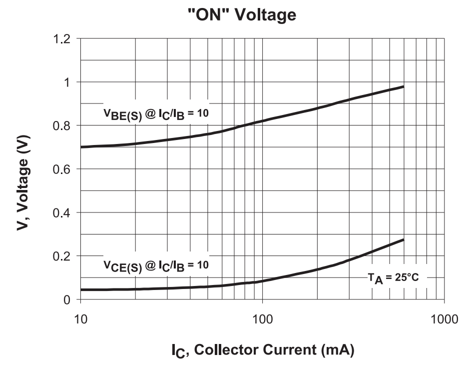
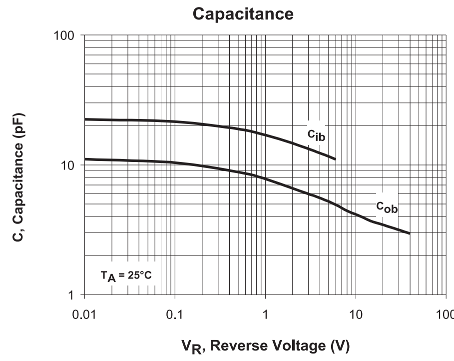
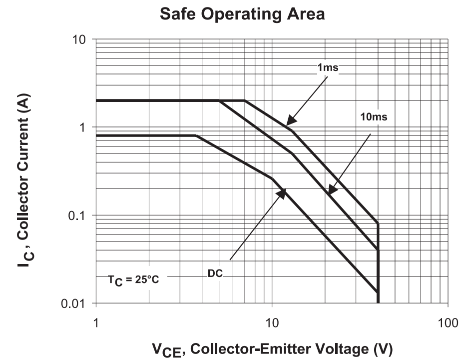
PROCESS CP225

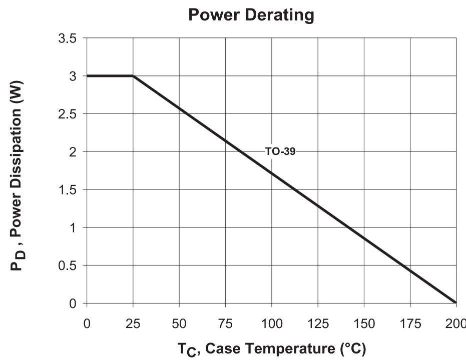
Typical Electrical Characteristics

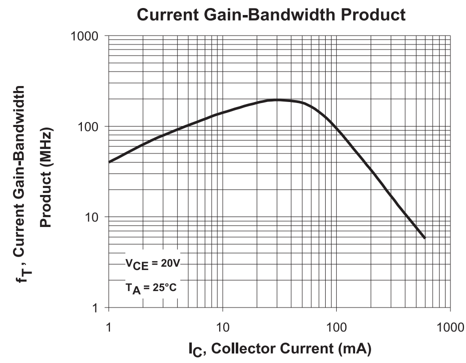












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